

(56)

References Cited

U.S. PATENT DOCUMENTS

2012/0062439	A1*	3/2012	Liao	H01L 23/481
				343/841
2012/0295539	A1*	11/2012	McCormack	H04B 5/0031
				455/39
2013/0225102	A1	8/2013	Tsutsumi et al.	
2014/0247195	A1	9/2014	Yen	
2015/0302290	A1	10/2015	Saito	
2017/0077039	A1*	3/2017	Liao	H01L 23/552

* cited by examiner

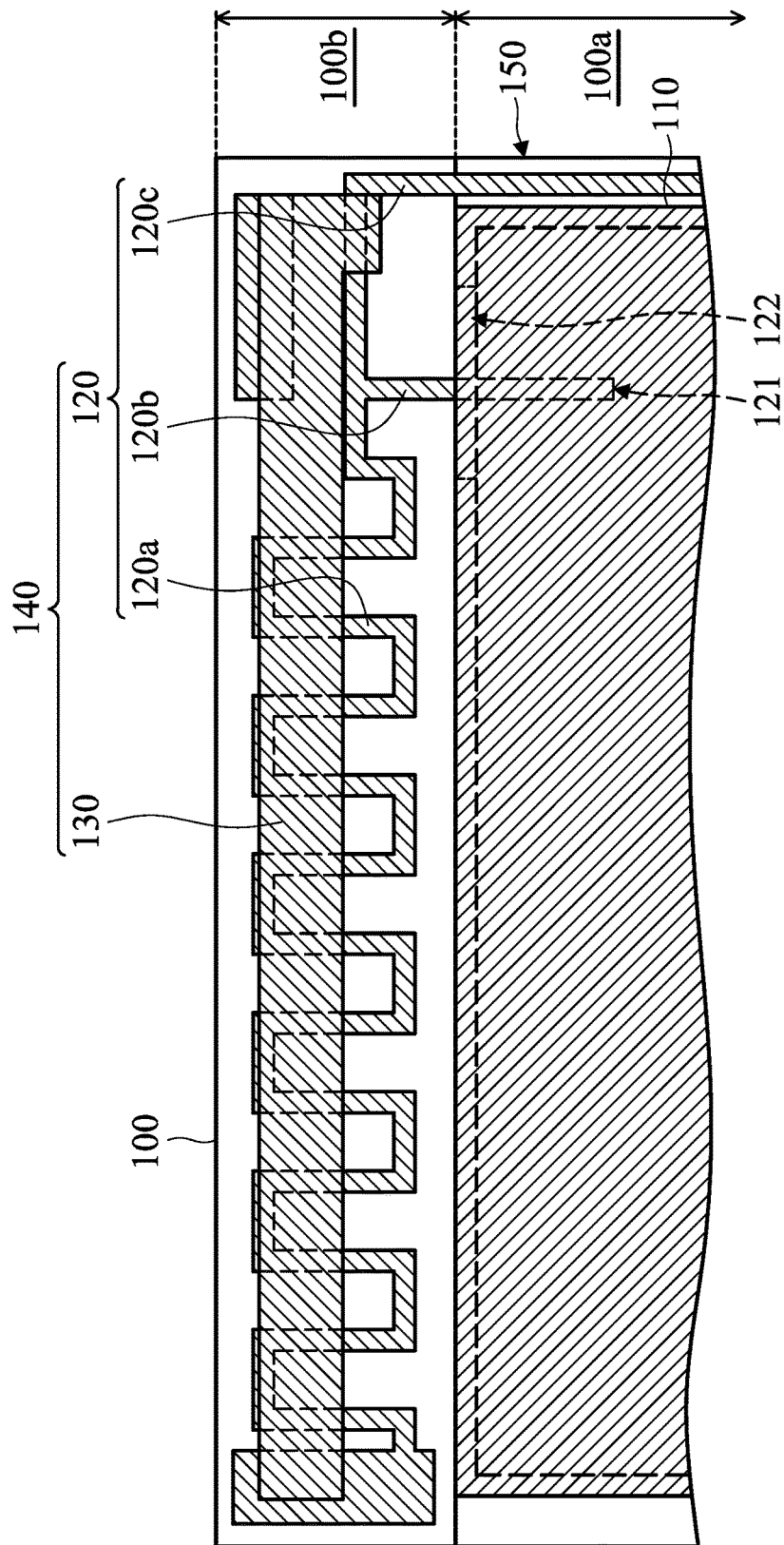


FIG. 1B

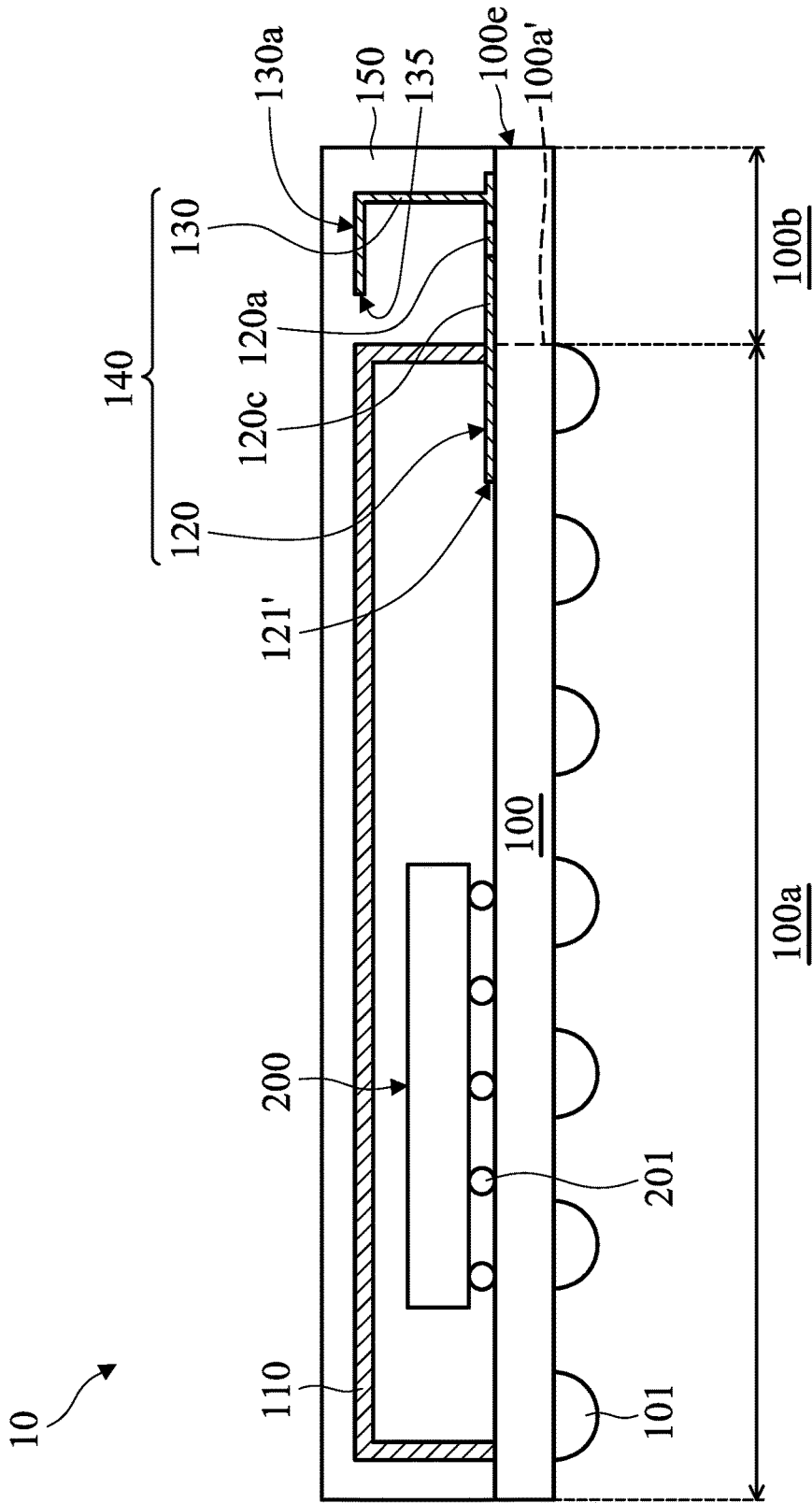


FIG. 1C

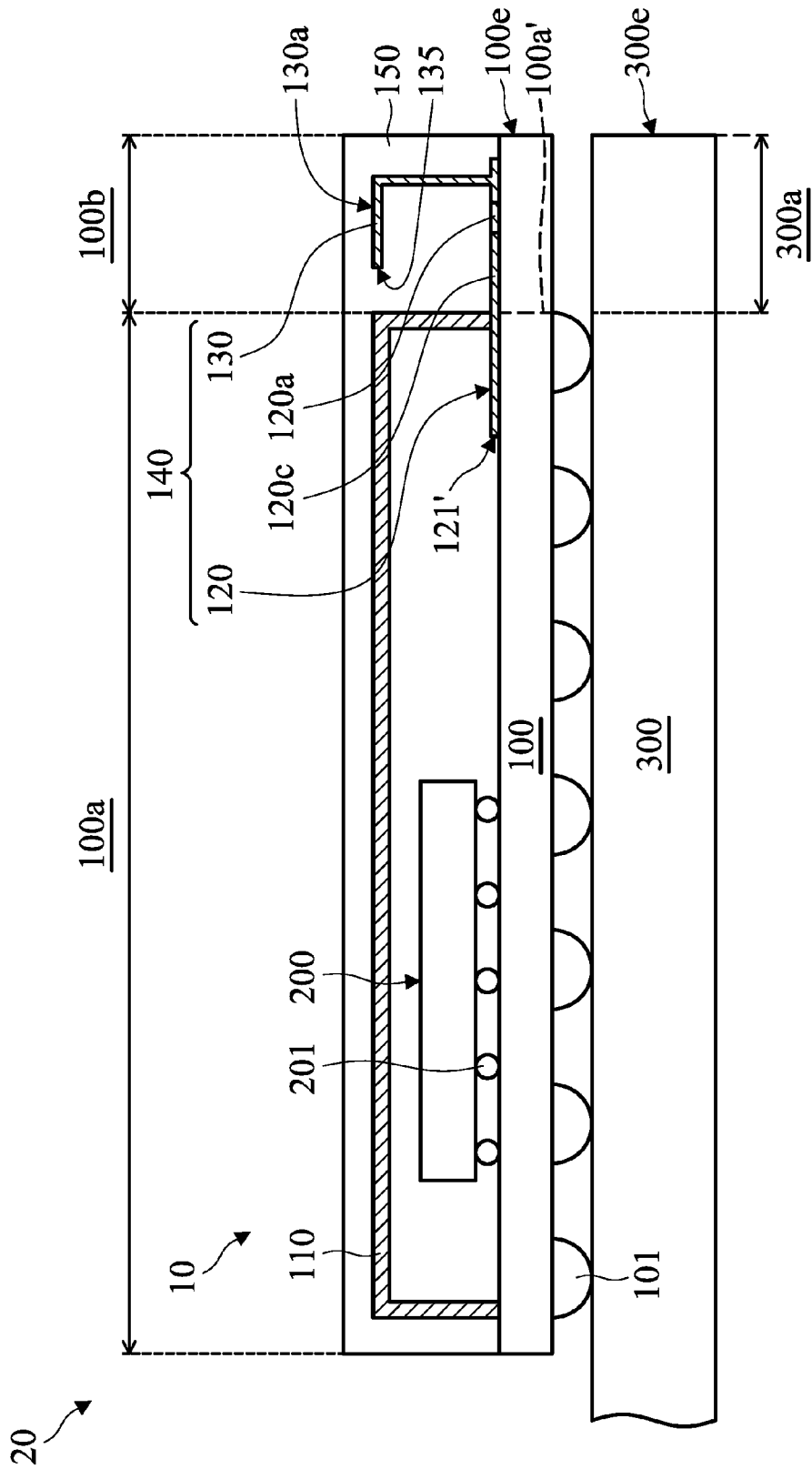


FIG. 2

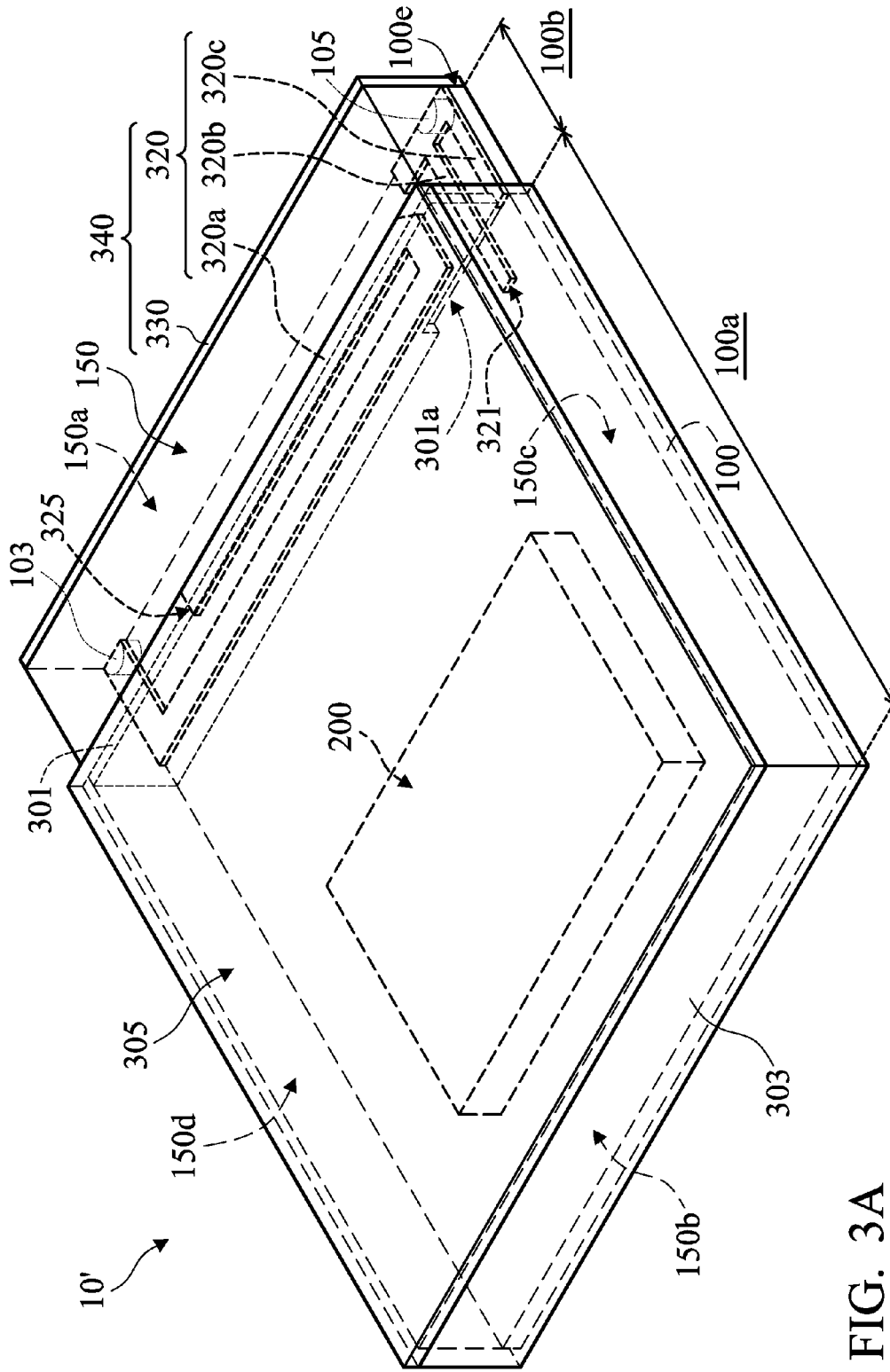


FIG. 3A

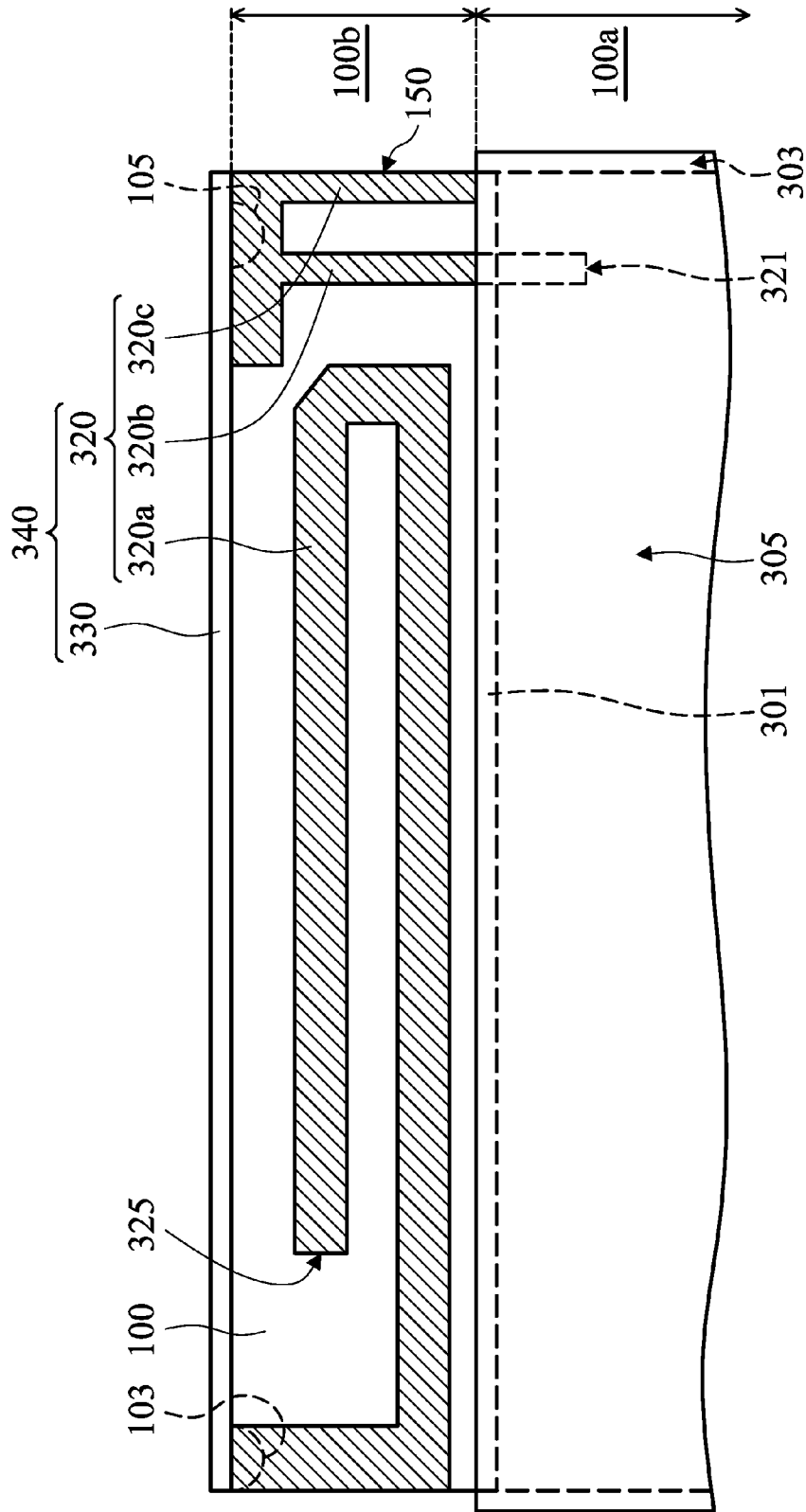


FIG. 3B

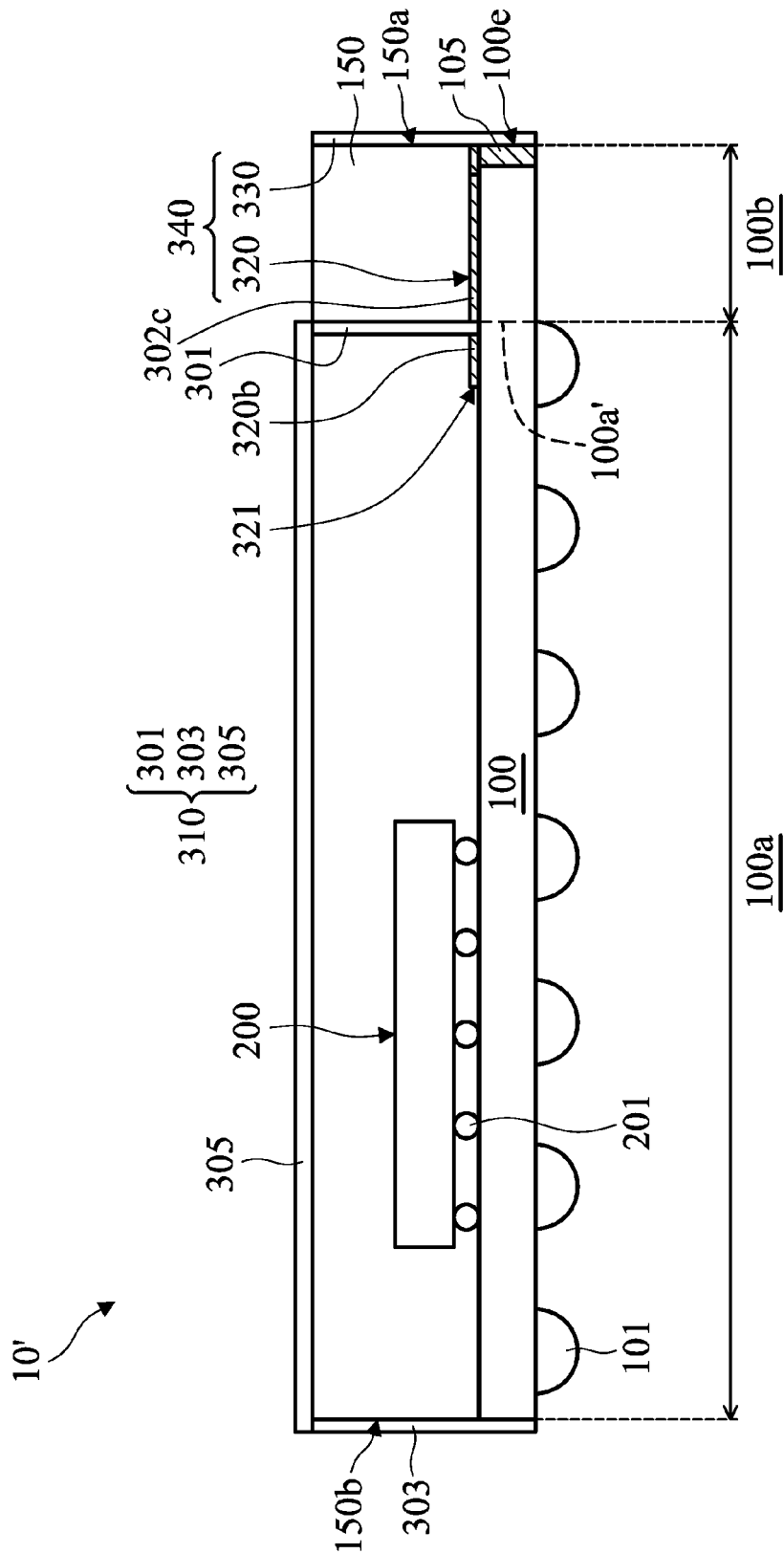


FIG. 3C

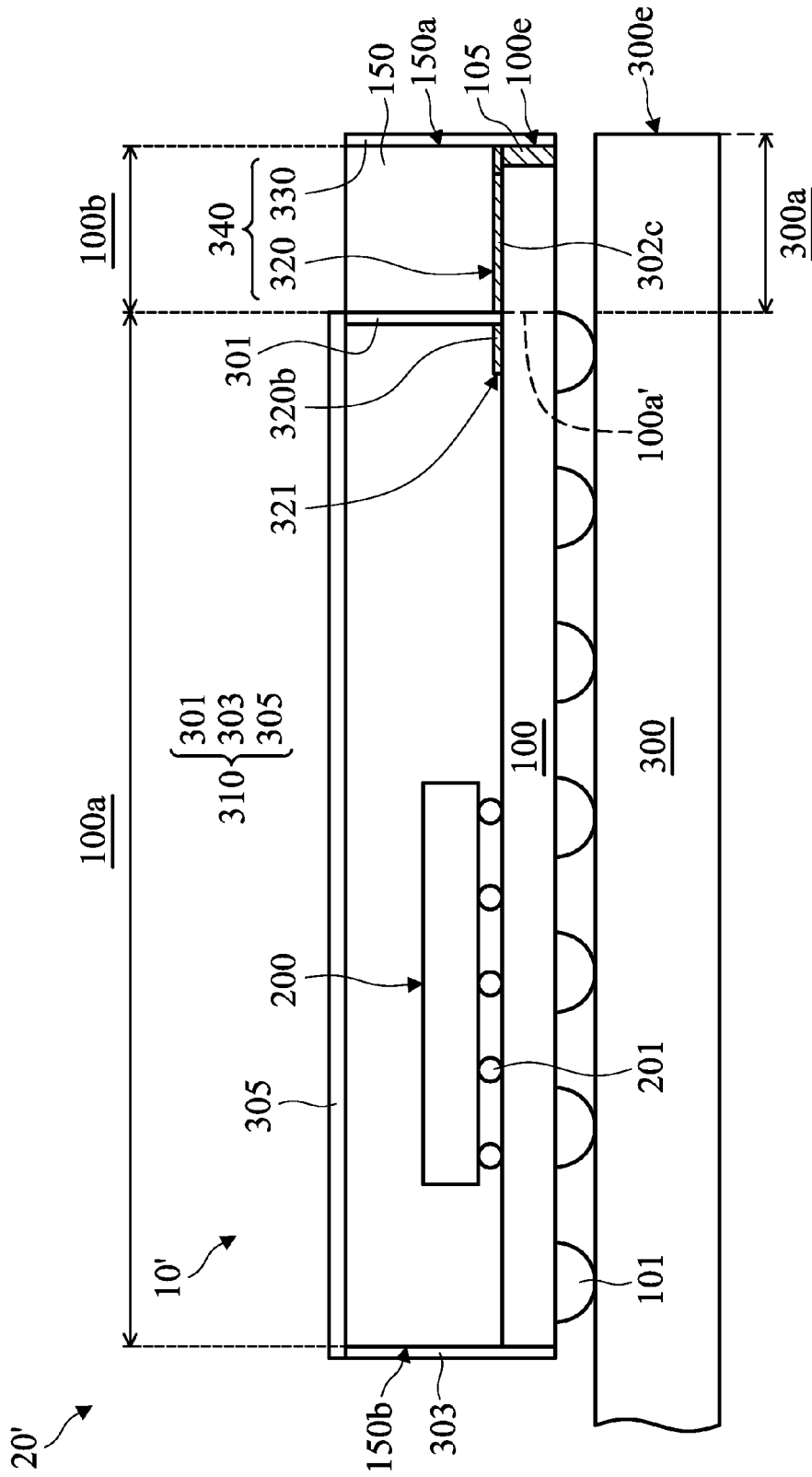


FIG. 4

SEMICONDUCTOR PACKAGE WITH THREE-DIMENSIONAL ANTENNA

CROSS REFERENCE TO RELATED APPLICATIONS

This application claims the benefit of U.S. Provisional Application No. 62/275,280 filed on Jan. 6, 2016, the entirety of which is incorporated by reference herein.

BACKGROUND OF THE INVENTION

Field of the Invention

The present invention relates to semiconductor package technology, and in particular to a semiconductor package with a three-dimensional (3D) antenna.

Description of the Related Art

In recent years, the semiconductor industry has seen a trend towards the so-called system in package (SiP) concept. The integration of systems integrated into a single integrated circuit (IC) package provides several advantages in terms of cost, size, performance, and product-design flexibility.

Many handheld electronic products, such as handheld computers, mobile phones, personal digital assistants (PDAs), and digital cameras, or media players, often include SiP components. These handheld electronic products are also provided with wireless communications capabilities. For achieving the function of wireless communications, an antenna and a communication module (e.g., an IC package with radio frequency (RF) devices) are typically required. The antenna is used for transmitting and receiving signals from the communication module.

In the conventional design of an IC package (e.g., the communication module), the antenna is not incorporated therein. Namely, the antenna and the IC package are manufactured separately and are electrically connected after being mounted on a circuit board. As a result, the manufacturing cost is increased and it is difficult to achieve a compact and small SiP component.

Although the incorporation of an antenna into a typical IC package has been proposed, electromagnetic interference (EMI) and signal coupling between the antenna and different parts of the chip or package may easily occur. These can result in a reduction of the antenna's level of performance. Thus, a novel semiconductor package is desirable.

BRIEF SUMMARY OF THE INVENTION

Semiconductor packages are provided. An exemplary embodiment of a semiconductor package includes a package substrate having a first region and a second region defined between an edge of the package substrate and an edge of the first region. A semiconductor die is disposed on the package substrate in the first region. A conductive shielding element is disposed on the package substrate and covers the semiconductor die. A 3D antenna includes a planar structure portion disposed on the package substrate in the second region. The 3D antenna further includes a bridge structure portion above the planar structure portion and connected thereto. A molding compound encapsulates the conductive shielding element and the 3D antenna.

Another exemplary embodiment of a semiconductor package includes a package substrate having a first region and a second region defined between an edge of the package substrate and an edge of the first region. A molding compound is disposed on the package substrate in the first and second regions. A semiconductor die is disposed on the

package substrate in the first region and inside the molding compound. A 3D antenna includes a planar structure portion on the package substrate in the second region. The 3D antenna further includes a wall structure portion contacting the planar structure portion and covering a top surface or one of sidewalls of the molding compound in the second region. A conductive shielding element includes a spacer portion between the 3D antenna and the semiconductor die and passing through the molding compound. The conductive shielding element further includes a U-shaped wall portion covering the sidewalls of the molding compound in the first region and separated from the wall structure portion of the 3D antenna.

An exemplary embodiment of a semiconductor package assembly includes a printed circuit board (PCB) having a keep-out region. A package substrate is disposed on the PCB. The semiconductor package includes a package substrate having a first region and a second region defined between an edge of the package substrate and an edge of the first region. A semiconductor die is disposed on the package substrate in the first region. A conductive shielding element is disposed on the package substrate and covers the semiconductor die. A 3D antenna includes a planar structure portion disposed on the package substrate in the second region. The 3D antenna further includes a bridge structure portion above the planar structure portion and connected thereto. A molding compound encapsulates the conductive shielding element and the 3D antenna.

Another exemplary embodiment of a semiconductor package assembly includes a PCB having a keep-out region. A package substrate is disposed on the PCB. The semiconductor package includes a package substrate having a first region and a second region defined between an edge of the package substrate and an edge of the first region. A molding compound is disposed on the package substrate in the first and second regions. A semiconductor die is disposed on the package substrate in the first region and inside the molding compound. A 3D antenna includes a planar structure portion on the package substrate in the second region. The 3D antenna further includes a wall structure portion contacting the planar structure portion and covering a top surface or one of sidewalls of the molding compound in the second region. A conductive shielding element includes a spacer portion between the 3D antenna and the semiconductor die and passing through the molding compound. The conductive shielding element further includes a U-shaped wall portion covering the sidewalls of the molding compound in the first region and separated from the wall structure portion of the 3D antenna.

A detailed description is given in the following embodiments with reference to the accompanying drawings.

BRIEF DESCRIPTION OF THE DRAWINGS

The present invention can be more fully understood by reading the subsequent detailed description and examples with references made to the accompanying drawings, wherein:

FIG. 1A is a perspective view of an exemplary semiconductor package in accordance with some embodiments of the disclosure.

FIG. 1B is a partial plan view of the exemplary semiconductor package shown in FIG. 1A.

FIG. 1C is a cross-sectional view of an exemplary semiconductor package shown in FIG. 1A.

3

FIG. 2 is a cross-sectional view of an exemplary semiconductor package assembly in accordance with some embodiments of the disclosure.

FIG. 3A is a perspective view of an exemplary semiconductor package in accordance with some embodiments of the disclosure.

FIG. 3B is a partial plan view of the exemplary semiconductor package shown in FIG. 3A.

FIG. 3C is a cross-sectional view of an exemplary semiconductor package shown in FIG. 3A.

FIG. 4 is a cross-sectional view of an exemplary semiconductor package assembly in accordance with some embodiments of the disclosure.

DETAILED DESCRIPTION OF THE INVENTION

The following description is of the best-contemplated mode of carrying out the invention. This description is made for the purpose of illustrating the general principles of the invention and should not be taken in a limiting sense. The scope of the invention is determined by reference to the appended claims.

The present invention will be described with respect to particular embodiments and with reference to certain drawings, but the invention is not limited thereto and is only limited by the claims. The described drawings are only schematic and are non-limiting. In the drawings, the size of some of the elements may be exaggerated for illustrative purposes and are not drawn to scale. The dimensions and the relative dimensions do not correspond to actual dimensions in the practice of the invention.

Refer to FIGS. 1A to 1C, in which FIG. 1A is a perspective view of a semiconductor package 10 in accordance with some embodiments of the disclosure, FIG. 1B is a partial plan view of the exemplary semiconductor package shown in FIG. 1A, and FIG. 1C is a cross-sectional view of an exemplary semiconductor package shown in FIG. 1A. In some embodiments, the semiconductor package 10 is a flip-chip semiconductor package. For example, the semiconductor package 10 may be a system in package (SiP) package with an integrated antenna, such as an antenna on package (AoP) or antenna in package (AiP).

In the embodiment, the semiconductor package 10 includes a package substrate 100 having a first region 100a and a second region 100b, as shown in FIG. 1C. The second region 100b is defined between an edge 100e of the package substrate 100 and an edge of the first region 100a' and has an area that is smaller than that of the first region 100a. In some embodiments, the package substrate 100 may be mounted on a base (not shown), such as a PCB, by a bonding process. For example, the package substrate 100 includes conductive structures 101 that are mounted on and electrically coupled to the base in the bonding process. In some embodiments, the conductive structures 101 include a conductive bump structure (such as a copper or solder bump structure), a conductive pillar structure, a conductive wire structure or a conductive paste structure.

In the embodiment, the semiconductor package 10 further includes a semiconductor die 200 disposed on the package substrate 100 in the first region 100a. In some embodiments, the semiconductor die 200 may be mounted on the package substrate 100 by a bonding process. For example, the semiconductor die 200 includes conductive structures 201 that are mounted on and electrically coupled to the package substrate 100 in the bonding process. The conductive structures 201 may include a conductive bump structure (such as

4

a copper or solder bump structure), a conductive pillar structure, or a conductive paste structure. In some embodiments, the semiconductor die may be a system on chip (SOC) die and include a radio frequency (RF) device (not shown) therein.

In the embodiment, the semiconductor package 10 further includes a conductive shielding element 110 disposed on the package substrate 100 and covers the semiconductor die 200. In some embodiments, the conductive shielding element 110 is formed of copper, aluminum or another suitable shielding material to provide EMI protection.

In some embodiments, the conductive shielding element 110 includes a plate portion and sidewall portions surrounding the edges of the plate portion, so that the semiconductor die 200 is inside the space created by the conductive shielding element 110 and the package substrate 100. In some embodiments, the conductive shielding element 110 has an opening 122 formed in one of the sidewall portions thereof. For example, the sidewall portion that extends along the edge 100a' (indicated in FIG. 1C) of the package substrate 100 has an opening 122 (indicated in FIG. 1A). The opening 122 allows one or more devices formed in the semiconductor package 10 to pass through the conductive shielding element 110. For example, an antenna may pass through the conductive shielding element 110 via the opening 122.

In the embodiment, the semiconductor package 10 further includes a 3D antenna 140 disposed on the package substrate 100. The 3D antenna 140 may include a planar structure portion 120 and a bridge structure portion 130. In some embodiments, the planar structure portion 120 is disposed on the package substrate 100 in the second region 100b. Moreover, the bridge structure portion 130 is disposed above the planar structure portion 120 and connected thereto.

In some embodiments, the planar structure portion 120 of the 3D antenna 140 includes a folded pattern 120a and first and second bar patterns 120b and 120c connected thereto, as shown in FIGS. 1A and 1B. In some embodiments, the folded pattern 120a of the planar structure portion 120 is entirely located at the second region 100b of the package substrate 100. Moreover, the first bar pattern 120b and the second bar pattern 120c of the planar structure portion 120 are located at both first and second regions 100a and 100b of the package substrate 100. For example, the first bar pattern 120b is extended from the folded pattern 120a of the planar structure portion 120 and passes through the opening 122 of the conductive shielding element 110, such that the first bar pattern 120b of the planar structure portion 120 has an end 121 in the first region 100a of the package substrate 100. Moreover, the second bar pattern 120c is also extended from the folded pattern 120a of the planar structure portion 120 to the first region 100a of the package substrate 100, such that the second bar pattern 120c of the planar structure portion 120 has an end 121' in the first region 100a of the package substrate 100. In this case, the end 121 of the first bar pattern 120b of the planar structure portion 120 serves as a feeding point of the 3D antenna 140. The second bar pattern 120c is grounded (not shown) via the package substrate 100 and may be parallel to the first bar pattern 120b.

In some embodiments, the bridge structure portion 130 of the 3D antenna 140 is also entirely located at the second region 100b of the package substrate 100 and has an inverted U shape, as shown in FIG. 1A. In this case, the inverted U-shaped bridge structure portion 130 may include a first end that is connected to and above the folded pattern 120a of the planar structure portion 120 and a second end sup-

5

ported by the package substrate **100**. Moreover, the inverted U-shaped bridge structure portion **130** may have a lateral extending portion **130a** (as indicated in FIG. 1C) that is parallel to the first and second bar patterns **120b** and **120c** of the planar structure portion **120** and has an end **135** to serve as an open end of the 3D antenna **140**.

In the embodiment, since the antenna is integrated in the semiconductor package **10** and disposed on a relatively small region of the package substrate **100** (e.g., the second region **100b**), the bridge structure portion **130** allows for the formation of a 3D antenna, so as to increase the effective length of the 3D antenna **140**. As a result, a desired operation frequency for the antenna can be obtained.

It should be understood that the shape of the bridge structure and of the planar structure portion of the 3D antenna may be varied by design demands and are not limited to the embodiment shown in FIGS. 1A to 1C.

In the embodiment, the semiconductor package **10** further includes a molding compound **150** disposed on the package substrate **100** and entirely encapsulates the conductive shielding element **110** and the 3D antenna **140** thereon. In some embodiments, the molding compound **150** may be formed of an epoxy, a resin, a moldable polymer, or the like.

Refer to FIG. 2, which is a cross-sectional view of an exemplary semiconductor package assembly **20** in accordance with some embodiments of the disclosure. Descriptions of elements of the embodiments that are the same as or similar to those previously described with reference to FIGS. 1A to 1C are hereinafter omitted for brevity. In the embodiment, the semiconductor package assembly **20** includes a semiconductor package **10** shown in FIGS. 1A to 1C. Moreover, the semiconductor package **10** is disposed on a circuit board **300** (e.g., a printed circuit board (PCB) that may be formed of polypropylene (PP)). For example, the semiconductor package **10** is mounted on the circuit board **300** by the conductive structures **101** of the package substrate **100** using a bonding process.

In some embodiments, the circuit board **300** (e.g., the PCB) has a keep-out region **300a** that is a region free of conductive traces or elements formed therein. Moreover, the semiconductor package **10** is disposed on the circuit board **300** in an arrangement wherein the second region **100b** of the package substrate **100** corresponds to the keep-out region **300a** of the circuit board **300**. Namely, the second region **100b** overlaps with the keep-out region **300a**. In some embodiments, the keep-out region **300a** is located near an edge **300e** of the circuit board **300**, such that the 3D antenna **140** is disposed near the edge **300e** of the circuit board **300**.

According to the foregoing embodiments, a conductive shielding element and a 3D antenna are integrated into a semiconductor package for fabricating an antenna in package (AiP). Since the 3D antenna is incorporated into the semiconductor package, the manufacturing cost is reduced and it allows for achieving a small, compact SiP component.

Moreover, the bridge structure portion of the 3D antenna increases its effective length further.

Moreover, since the 3D antenna is embedded in the molding compound, design flexibility for the system integration of the semiconductor package can be increased.

Additionally, the conductive shielding element provides an EMI protection for the semiconductor package and prevents signal coupling between the antenna and semiconductor die that is inside the conductive shielding element.

Refer to FIGS. 3A to 3C, in which FIG. 3A is a perspective view of a semiconductor package **10'** in accordance with some embodiments of the disclosure, FIG. 3B is a partial plan view of the exemplary semiconductor package shown

6

in FIG. 3A, and FIG. 3C is a cross-sectional view of an exemplary semiconductor package shown in FIG. 3A. Descriptions of elements of the embodiments hereinafter that are the same as or similar to those previously described with reference to FIGS. 1A to 1C are omitted for brevity. In the embodiment, the semiconductor package **10'** has a structure that is similar to that of the semiconductor package **10** shown in FIGS. 1A to 1C except for the structure and the arrangement of the conductive shielding element and the 3D antenna.

In the embodiment, the semiconductor package **10'** includes a molding compound **150** disposed on a package substrate **100** in the first and second regions **100a** and **100b**. Moreover, a semiconductor die **200** disposed on the package substrate **100** in the first region **100a** and inside the molding compound **150**.

In the embodiment, the semiconductor package **10'** further includes a 3D antenna **340** disposed on the package substrate **100**. The 3D antenna **340** includes a planar structure portion **320** and a wall structure portion **330** contacting the planar structure portion **320**. In some embodiments, the planar structure portion **320** is disposed on the package substrate **100** in the second region **100b**. Moreover, the wall structure portion **330** covers one or more sidewalls **150a**, **150c**, and **150d** of the molding compound **150** in the second region **100b** (e.g., the sidewall **150a** indicated in FIGS. 3A and 3C that is near the edge **100e** of the package substrate **100**). In some embodiments, the wall structure portion **330** may cover the top surface of the molding compound **150** in the second region **100b**.

In some embodiments, the planar structure portion **320** of the 3D antenna **140** includes a spiral pattern **320a** and two bar patterns **320b** and **320c** separated therefrom, as shown in FIGS. 3A and 3B. In some embodiments, the spiral pattern **320a** of the planar structure portion **320** is entirely located at the second region **100b** of the package substrate **100** and has an end **325** to serve as an open end of the 3D antenna **340**.

In some embodiments, the bar pattern **320b** of the planar structure portion **120** is T-shaped and located at both first and second regions **100a** and **100b** of the package substrate **100**. For example, the bar pattern **320b** (e.g., T-bar pattern) has a stem portion extending from the second region **100b** of the package substrate **100** to the first region **100a** thereof. The stem portion of the bar pattern **320b** has an end **321** in the first region **100a** of the package substrate **100**. In this case, the end **321** of the bar pattern **320b** of the planar structure portion **320** serves as a feeding point of the 3D antenna **340**. Moreover, the bar pattern **320b** (e.g., T-bar pattern) has an arm portion. The bar pattern **320c** is extended from the arm portion of the bar pattern **320b** and may be parallel to the stem portion of the bar pattern **320b**. In this case, the bar pattern **320c** is located at second region **100b** of the package substrate **100** and may be grounded (not shown) via the package substrate **100**.

In some embodiments, the 3D antenna **340** may further include first and second conductive vias **103** and **105** (indicated in FIGS. 3A and 3C) that are disposed in the package substrate **100** in the second region **100b** and electrically connected to the spiral pattern **320a** and the bar pattern **320b**, respectively. In this case, each of the first and second conductive vias **103** and **105** has a sidewall level with the edge **100e** of the package substrate **100**, such that the sidewalls of the first and second conductive vias **103** and **105** are exposed from the edge **100e** of the package substrate **100**.

Moreover, the wall structure portion **330** of the 3D antenna **340** may further cover the sidewall of the package substrate **100** that is at the edge **100e** of the package substrate **100**, so that the exposed sidewalls of the first and second conductive vias **103** and **105** contact the wall structure portion **330** of the 3D antenna **340**. As a result, the first conductive via **103** is electrically connected between the spiral pattern **320a** and the wall structure portion **330** and the second conductive via **105** is electrically connected between the bar pattern **320b** and the wall structure portion **330**.

Similarly, in the embodiment, the wall structure portion **330** allows for the formation of a 3D antenna, so as to increase the effective length. As a result, a desired operation frequency for the antenna can be obtained.

It should be understood that the shape of the planar structure portion of the 3D antenna may be varied by design demands and is not limited to the embodiment shown in FIGS. **3A** to **3C**.

In the embodiment, the semiconductor package **10'** further includes a conductive shielding element **310** disposed on the package substrate **100** to cover the semiconductor die **200**. In some embodiments, the conductive shielding element **310** is formed of copper, aluminum or another suitable shielding material to provide an EMI protection. In some embodiments, the conductive shielding element **310** may be formed of a material that is the same as that of the wall structure portion **330** of the 3D antenna **340**.

In the embodiment, the conductive shielding element **310** includes a spacer portion **301**, a U-shaped wall portion **303**, and a plate portion **305**. In some embodiments, the spacer portion **301** of the conductive shielding element **310** is disposed on the package substrate **100** and extends along the edge **100a'** (indicated in FIG. **3C**) of the package substrate **100**. Moreover, the spacer portion **301** of the conductive shielding element **310** is disposed between the 3D antenna **340** and the semiconductor die **200** and passes through the molding compound **105**, such that the top surface of the spacer portion **301** is exposed from the molding compound **105**. In some embodiments, sidewalls of the spacer portion **301** may also be exposed from the sidewalls **105c** and **105d** (indicated in FIG. **3A**) of the molding compound **105**. In some embodiments, the spacer portion **301** of the conductive shielding element **310** has an opening **301a** formed therein. The opening **301a** allows one or more devices formed in the semiconductor package **10** to pass through the conductive shielding element **110**. For example, the bar pattern **320b** of the planar structure portion **320** of the 3D antenna **340** may pass through the spacer portion **301** of the conductive shielding element **110** via the opening **301a**.

In some embodiments, the U-shaped wall portion **303** covers the sidewalls **150b**, **150c**, and **150d** of the molding compound **150** in the first region **100a** and is separated from the wall structure portion **330** of the 3D antenna **340**. Namely, portions of the sidewalls **150c** and **150d** may be exposed from the U-shaped wall portion **303**.

In some embodiments, the plate portion **305** partially covers a top surface of the molding compound **105** in the first region **100a**, so that the plate portion **305** is connected to the exposed top surface of the spacer portion **301**. Similarly, the plate portion **305** is separated from the wall structure portion **330** of the 3D antenna **340**. Namely, a portion of the top surface of the molding compound **105** may be exposed from the plate portion **305**.

Refer to FIG. **4**, a cross-sectional view of an exemplary semiconductor package assembly **20'** in accordance with some embodiments of the disclosure. Descriptions of elements of the embodiments hereinafter that are the same as or

similar to those previously described with reference to FIGS. **2** and **3A** to **3C** are omitted for brevity. In the embodiment, the semiconductor package assembly **20'** includes a semiconductor package **10'** shown in FIGS. **3A** to **3C**. Moreover, the semiconductor package **10'** is disposed on a circuit board **300**. For example, the semiconductor package **10'** is mounted on the circuit board **300** by the conductive structures **101** of the package substrate **100** using a bonding process.

In some embodiments, the semiconductor package **10'** is disposed on the circuit board **300** in an arrangement wherein the second region **100b** of the package substrate **100** corresponds to the keep-out region **300a** of the circuit board **300**. Namely, the second region **100b** overlaps with the keep-out region **300a**. In some embodiments, the keep-out region **300a** is located near an edge **300e** of the circuit board **300**, such that the 3D antenna **340** is disposed near the edge **300e** of the circuit board **300**.

According to the foregoing embodiments, a conductive shielding element and a 3D antenna are integrated into a semiconductor package for fabricating an antenna in package (AiP). Since the 3D antenna is incorporated into the semiconductor package, the manufacturing cost is reduced and it allows for achieving a small, compact SiP component.

Moreover, the wall structure portion of the 3D antenna increases its effective length. As a result, a desired operation frequency for the antenna can be obtained.

Moreover, since the 3D antenna is integrated in the semiconductor package, design flexibility for the system integration of the semiconductor package can be increased.

Additionally, the conductive shielding element provides EMI protection for the semiconductor package and prevents signal coupling between the antenna and semiconductor die that is inside the conductive shielding element.

While the invention has been described by way of example and in terms of the preferred embodiments, it should be understood that the invention is not limited to the disclosed embodiments. On the contrary, it is intended to cover various modifications and similar arrangements (as would be apparent to those skilled in the art). Therefore, the scope of the appended claims should be accorded the broadest interpretation so as to encompass all such modifications and similar arrangements.

What is claimed is:

1. A semiconductor package, comprising:
 - a package substrate having a first region and a second region defined between an edge of the package substrate and an edge of the first region;
 - a semiconductor die disposed on the package substrate in the first region;
 - a conductive shielding element disposed on the package substrate and covering the semiconductor die;
 - a three-dimensional (3D) antenna, comprising:
 - a planar structure portion disposed on the package substrate in the second region; and
 - a bridge structure portion above the planar structure portion and connected thereto; and
 - a molding compound encapsulating the conductive shielding element and the 3D antenna.
2. The semiconductor package as claimed in claim 1, wherein the planar structure portion of the 3D antenna comprises a folded pattern and first and second bar patterns connected thereto.
3. The semiconductor package as claimed in claim 2, wherein the first bar pattern has an end in the first region to serve as a feeding point of the 3D antenna.

9

4. The semiconductor package as claimed in claim 2, wherein the second bar pattern is parallel to the first bar pattern and grounded via the package substrate.

5. The semiconductor package as claimed in claim 2, wherein the conductive shielding element has an opening in a sidewall thereof, such that the first bar pattern passes through the conductive shielding element via the opening.

6. The semiconductor package as claimed in claim 1, wherein the bridge structure of the 3D antenna has an end to serve as an open end of the 3D antenna.

7. A semiconductor package, comprising:

a package substrate having a first region and a second region defined between an edge of the package substrate and an edge of the first region;

a molding compound disposed on the package substrate in the first and second regions;

a semiconductor die disposed on the package substrate in the first region and inside the molding compound;

a three-dimensional (3D) antenna, comprising:

a planar structure portion on the package substrate in the second region; and

a wall structure portion contacting the planar structure portion and covering a top surface or one of sidewalls of the molding compound in the second region; and

a conductive shielding element comprising:

a spacer portion between the 3D antenna and the semiconductor die and passing through the molding compound; and

a U-shaped wall portion covering the sidewalls of the molding compound in the first region and separated from the wall structure portion of the 3D antenna.

8. The semiconductor package as claimed in claim 7, wherein the planar structure portion of the 3D antenna comprises a spiral pattern and a bar pattern separated therefrom.

9. The semiconductor package as claimed in claim 8, wherein the bar pattern has one end in the first region to serve as a feeding point of the 3D antenna.

10. The semiconductor package as claimed in claim 8, wherein the spiral pattern has an end to serve as an open end of the 3D antenna.

11. The semiconductor package as claimed in claim 8, wherein the spacer portion of the conductive shielding element has an opening, such that the bar pattern passes through the spacer portion via the opening.

12. The semiconductor package as claimed in claim 8, wherein the 3D antenna further comprises first and second conductive vias that are disposed in the package substrate in the second region and exposed from the edge of the package substrate.

13. The semiconductor package as claimed in claim 12, wherein the first conductive via is electrically connected between the spiral pattern and the wall structure portion and the second conductive via is electrically connected between the bar pattern and the wall structure portion.

14. The semiconductor package as claimed in claim 7, wherein the conductive shielding element further comprises a plate portion covering a top surface of the molding compound in the first region, connected to the spacer portion, and separated from the wall structure portion of the 3D antenna.

15. A semiconductor package assembly, comprising:

a printed circuit board (PCB) having a keep-out region;

a package substrate disposed on the PCB, wherein the package substrate has a first region and a second region

10

defined between an edge of the package substrate and an edge of the first region and corresponding to the keep-out region;

a semiconductor die disposed on the package substrate in the first region;

a conductive shielding element disposed on the package substrate and covering the semiconductor die;

a three-dimensional (3D) antenna, comprising:

a planar structure portion disposed on the package substrate in the second region; and

a bridge structure portion above the planar structure portion and connected thereto; and

a molding compound encapsulating the conductive shielding element and the 3D antenna.

16. The semiconductor package assembly as claimed in claim 15, wherein the planar structure portion of the 3D antenna comprises a folded pattern and first and second bar patterns connected thereto.

17. The semiconductor package assembly as claimed in claim 16, wherein the first bar pattern has an end in the first region to serve as a feeding point of the 3D antenna and the second bar pattern is parallel to the first bar pattern and grounded via the package substrate.

18. The semiconductor package assembly as claimed in claim 16, wherein the conductive shielding element has an opening in a sidewall thereof, such that the first bar pattern passes through the conductive shielding element via the opening.

19. The semiconductor package assembly as claimed in claim 15, wherein the keep-out region is located near an edge of the PCB.

20. A semiconductor package assembly, comprising:

a printed circuit board (PCB) having a keep-out region;

a package substrate disposed on the PCB, wherein the package substrate has a first region and a second region defined between an edge of the package substrate and an edge of the first region and corresponding to the keep-out region;

a molding compound disposed on the package substrate in the first and second regions;

a semiconductor die disposed on the package substrate in the first region and inside the molding compound;

a three-dimensional (3D) antenna, comprising:

a planar structure portion on the package substrate in the second region; and

a wall structure portion contacting the planar structure portion and covering a top surface or one of sidewalls of the molding compound in the second region; and

a conductive shielding element comprising:

a spacer portion between the 3D antenna and the semiconductor die and passing through the molding compound; and

a U-shaped wall portion covering the sidewalls of the molding compound in the first region and separated from the wall structure portion of the 3D antenna.

21. The semiconductor package assembly as claimed in claim 20, wherein the planar structure portion of the 3D antenna comprises a spiral pattern and a bar pattern separated therefrom.

22. The semiconductor package assembly as claimed in claim 21, wherein the bar pattern has one end in the first region to serve as a feeding point of the 3D antenna and the spiral pattern has an end to serve as an open end of the 3D antenna.

23. The semiconductor package assembly as claimed in claim 21, wherein the spacer portion of the conductive

shielding element has an opening, such that the bar pattern passes through the spacer portion via the opening.

24. The semiconductor package assembly as claimed in claim 21, wherein the 3D antenna further comprises first and second conductive vias that are disposed in the package substrate in the second region and exposed from the edge of the package substrate, and wherein the first conductive via is electrically connected between the spiral pattern and the wall structure portion and the second conductive via is electrically connected between the bar pattern and the wall structure portion.

25. The semiconductor package assembly as claimed in claim 20, wherein the conductive shielding element further comprises a plate portion covering a top surface of the molding compound in the first region, connected to the spacer portion, and separated from the wall structure portion of the 3D antenna.

26. The semiconductor package assembly as claimed in claim 20, wherein the keep-out region is located near an edge of the PCB.

* * * * *